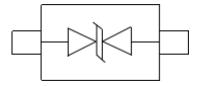
Description

The JS45B1GS30-2L is a bi-directional high power TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The JS45B1GS30-2L complies with the IEC 61000 -4-2 (ESD) standard with \pm 30kV air and \pm 30kV contact discharge. It is assem- bled into an ultra-small lead-free SOD-323 pack- age. The small size and high ESD surge protection make JS45B1GS30-2L an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Circuit Diagram



Circuit and Pin Schematic

Marking Diagram



Transparent top view 48D:Device Marking Code



Features

- * 1350W peak pulse power (8/20µs)
- * Low leakage:nA level
- * Operating voltage: 4.5V
- * Ultra low clamping voltage
- * One power line protects
- * Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test

Air discharge: ±30kV

Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 100A (8/20µs)
- * RoHS Compliant
- Package: SOD-323

Applications

- * Fast-charge battery chargers
- * Power management system
- * Cellular Handsets and Accessories
- Personal Digital Assistants
- * Notebooks and Handhelds
- * Portable Instrumentation
- * Digital Cameras

Ordering Information

Part Number	Packaging	Reel Size
JS45B1GS30-2L	3000/Tape & Reel	7 inch



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

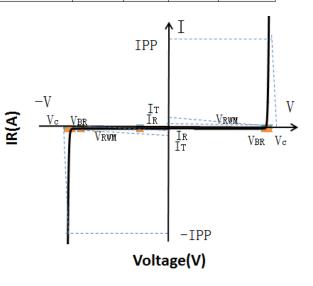
Parameter	Symbol	Value	Unit	
Peak Pulse Power (8/20µs)	Ppk	1350	W	
Peak Pulse Current (8/20µs)	IPP	100	А	
ESD per IEC 61000-4-2 (Air)	VESD	±30	kV	
ESD per IEC 61000-4-2 (Contact)	VESD	± 30	ΚV	
Operating Temperature Range	TJ	-55 to +125	°C	
Storage Temperature Range	Tstg	-55 to +150	°C	

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Reverse Working Voltage	Vrwm				4.5	V
Breakdown Voltage	Vbr	$I_T = 1mA$	4.7			V
Reverse Leakage Current	I _R	$V_{RWM} = 4.5V$			1	uA
Clamping Voltage	Vc	$I_{PP} = 20A (8 \times 20\mu s \text{ pulse})$			7.8	V
Clamping Voltage	Vc	$I_{PP} = 100A (8 \times 20 \mu s \text{ pulse})$			13.5	V
Junction Capacitance	Сл	VR = 0V, f = 1MHz			300	pF

Portion Electronics Parameter

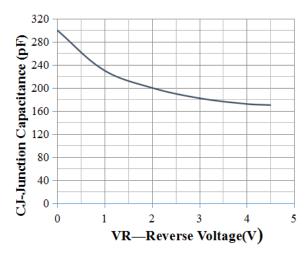
Symbol	Parameter	
Іт	Test Current	
Ірр	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @Ic	



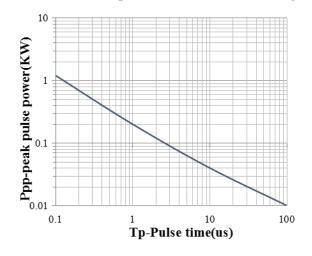
JS45B1GS30-2L



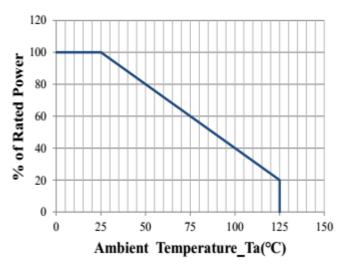
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



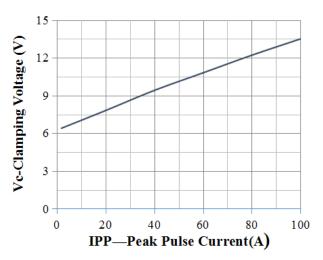
Junction Capacitance vs. Reverse Voltage



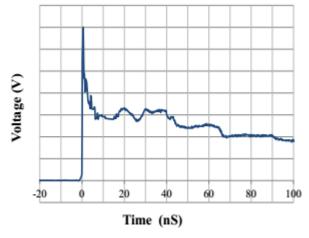
Peak Pulse Power vs. Pulse Time



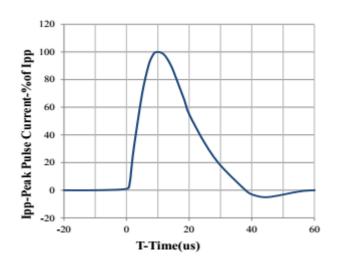
Power Derating Curve



Clamping Voltage vs. Peak Pulse Current



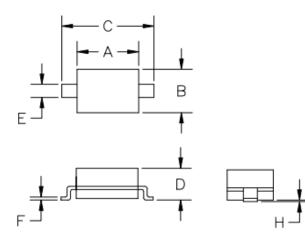
IEC61000-4-2 Pulse Waveform



8 X 20us Pulse Waveform

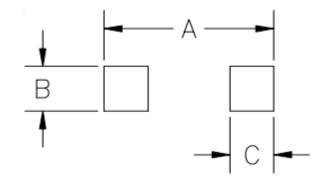


SOD-323 Package Outline Drawing (Dimensions in millimeters)



	DIMENSIONS			
SYM	MILLIMETERS		INC	HES
••••	MIN	MAX	MIN	MAX
Α	1.50	1.80	0.060	0.071
В	1.20	1.40	0.045	0.054
С	2.30	2.70	0.090	0.107
D	-	1.10	-	0.043
E	0.30	0.40	0.012	0.016
F	0.10	0.25	0.004	0.010
н	-	0.10	-	0.004

Suggested Land Pattern



SYM	DIMENSIONS		
511	MILLIMETERS	INCHES	
А	3.15	0.120	
в	0.80	0.031	
С	0.80	0.031	

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